

Bismuth chalcogenides topological insulators crystals grown by optical floating zone technique

Guarino A^{1, *}, Arumugam, R¹, Fittipaldi R¹, Lettieri M.¹, Balakrishnan G², Vecchione A¹.

*lead presenter: anita.guarino@spin.cnr.it

1 CNR-SPIN Salerno c/o University of Salerno, via Giovanni Paolo II 132, Fisciano, Italy

2 Department of Physics, University of Warwick, Coventry CV4 7AL, United Kingdom

Bismuth telluride and bismuth selenides are functional thermoelectric materials for low- and near-room temperature applications because of their low thermal conductivity and high weighted mobility [1]. In last decade, a large effort has been devoted to the study of this family of materials due to their excellent topological properties [2,3]. The development of a growth method to obtain pure materials with on-demand band gap is of utmost importance to investigate the equilibrium and out-of-equilibrium properties of low bandgap and metallic samples. For this purpose, the availability of Bi₂Se₃ samples with Sb/Te substitution can be beneficial to study the nonlinear properties of solids by high-order harmonic generation spectroscopy, allowing the tuning of the bandgap in the 200-300 meV range. In this framework, high quality single crystals of pure Bi₂Se₃ and Bi₂Te₃ as well as crystals with optimum concentrations of Sb and/or Te have been grown by optical floating zone technique in order to improve the electrical properties and/or to increase the band gap amplitude. Detailed characterization of the crystals has been systematically performed on the different sets of samples obtained, to investigate the quality of the crystals.

References

- [1] Hegde G S and Prabhu A N A Review on Doped/Composite Bismuth Chalcogenide Compounds for Thermoelectric Device Applications: Various Synthesis Techniques and Challenges J. Electr. Mat. 2022; 51; 2014-2042.
- [2] Mazumder J et al. A brief review of Bi₂Se₃ based topological insulator: From fundamentals to applications J Alloy and Comp. 2021; 888; 161492-161517.
- [3] M M Sharma et al. Comprehensive review on topological superconducting materials and interfaces Supercond. Sci. Technol. 2022; 35; 083003-083035.